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Claims

[c1] 1. A method for forming a display of active matrix organic light emitting diode (AMOLED), comprising:
providing a substrate having a light-emitting region and a non-light-emitting region, wherein the light-emitting region of the substrate has a plurality of pixel structures formed thereon;
forming a driving circuit on the substrate in the non-light-emitting region, wherein the driving circuit is electrically coupled with the pixel structures; and
adhering a packaging cap on the substrate, wherein the packaging cap covers the light-emitting region but the driving circuit remains being exposed.

[c2] 2. The method of claim 1, wherein the packaging cap comprises a metallic packaging cap or a glass packaging cap.

[c3] 3. The method of claim 1, wherein each of the pixel structures comprises an active device with an anode layer, a light-emitting layer, and a cathode layer.

[c4] 4. The method of claim 3, wherein the active device comprises being formed with at least two amorphous

silicon thin film transistors or at least two low temperature polysilicon thin film transistors.

[c5] 5. The method of claim 1, wherein the driving circuit comprises a plurality of thin film transistors.

[c6] 6. The method of claim 1, wherein the driving circuit comprises a plurality of thin film transistors and a single-crystal silicon semiconductor circuit.

[c7] 7. The method of claim 1, in the step of forming the driving circuit further comprising forming a plurality of conductive lines to electrically couple the driving circuit and the pixel structures.

[c8] 8. A display structure of active matrix organic light emitting diode (AMOLED), the display structure comprising:
a substrate having a light-emitting region and a non-light-emitting region, wherein the light-emitting region of the substrate has a plurality of pixel structures formed thereon;
a driving circuit, disposed on the substrate in the non-light-emitting region, wherein the driving circuit is electrically coupled with the pixel structures; and
a packaging cap, adhered on the substrate, wherein the packaging cap covers the light-emitting region but the driving circuit remains being exposed.

[c9] 9. The display structure of claim 8, wherein the packaging cap comprises a metallic packaging cap or a glass packaging cap.

[c10] 10. The display structure of claim 8, wherein each of the pixel structures comprises an active device with an anode layer, a light-emitting layer, and a cathode layer.

[c11] 11. The display structure of claim 8, wherein the active device comprises at least two amorphous silicon thin film transistors or at least two low temperature polysilicon thin film transistors.

[c12] 12. The display structure of claim 8, wherein the driving circuit comprises a plurality of thin film transistors.

[c13] 13. The display structure of claim 8, wherein the driving circuit comprises a plurality of thin film transistors and a single-crystal silicon semiconductor circuit.

[c14] 14. The display structure of claim 8, further comprising a plurality of conductive lines electrical coupled between the driving circuit and the pixel structures.